

N-channel TrenchMOS logic level FET Rev. 03 — 4 June 2010

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

Suitable for logic level gate drive sources

Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

| Table 1. | Quick reference | data | | | | | |
|-------------------|--|--|------------|-----|-----|-----|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | - | 55 | V |
| I _D | drain current | V _{GS} = 5 V; T _{mb} = 25 °C; see <u>Figure 3</u> ; see <u>Figure 1</u> | <u>[1]</u> | - | - | 75 | A |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | | - | - | 300 | W |
| Static cha | aracteristics | | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 12</u> | | - | 3.5 | 4.2 | mΩ |
| | | V_{GS} = 10 V; I _D = 25 A; T _j = 25 °C | | - | 3.1 | 3.7 | mΩ |
| Avalanch | e ruggedness | | | | | | |

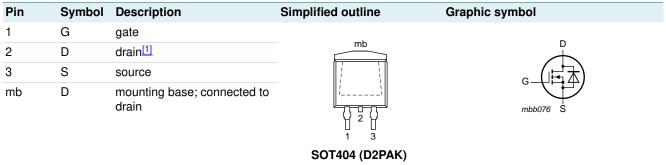
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| Table 1. | Quick reference data continued | | | | | |
|----------------------|--|--|-----|-----|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | $ \begin{split} I_D &= 75 \text{ A}; \ V_{sup} \leq 55 \text{ V}; \\ R_{GS} &= 50 \ \Omega; \ V_{GS} = 5 \text{ V}; \\ T_{j(init)} &= 25 \ ^\circ\text{C}; \ unclamped \end{split} $ | - | - | 1.2 | J |
| Dynamic | characteristics | | | | | |
| Q _{GD} | gate-drain charge | $V_{GS} = 5 V; I_D = 25 A;$ $V_{DS} = 44 V; T_j = 25 °C;$ see <u>Figure 13</u> | - | 37 | - | nC |

[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information



[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3.Ordering information

| Type number | Package | | |
|--------------|---------|--|---------|
| | Name | Description | Version |
| BUK964R2-55B | D2PAK | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404 |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------------|--|---|------------|-----|-----|-----|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | | - | - | 55 | V |
| V _{DGR} | drain-gate voltage | $R_{GS} = 20 \text{ k}\Omega$ | | - | - | 55 | V |
| V _{GS} | gate-source voltage | | | -15 | - | 15 | V |
| | drain current | $T_{mb} = 25 \text{ °C}; V_{GS} = 5 \text{ V}; \text{ see } \frac{\text{Figure 3}}{\text{Figure 1}};$ see $\frac{\text{Figure 1}}{1}$ | <u>[1]</u> | - | - | 75 | Α |
| | | T_{mb} = 100 °C; V_{GS} = 5 V; see <u>Figure 1</u> | [1] | - | - | 75 | А |
| | | T_{mb} = 25 °C; V_{GS} = 5 V; see <u>Figure 1</u> ; see <u>Figure 3</u> | [2] | - | - | 191 | Α |
| I _{DM} | peak drain current | T_{mb} = 25 °C; $t_p \le 10 \ \mu$ s; pulsed; see <u>Figure 3</u> | | - | - | 765 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | | - | - | 300 | W |
| T _{stg} | storage temperature | | | -55 | - | 175 | °C |
| Tj | junction temperature | | | -55 | - | 175 | °C |
| Source-drain | diode | | | | | | |
| ls | source current | T _{mb} = 25 °C | <u>[1]</u> | - | - | 75 | А |
| | | | [3] | - | - | 191 | А |
| I _{SM} | peak source current | $t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$ | | - | - | 765 | А |
| Avalanche ru | ggedness | | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | $\label{eq:ID} \begin{array}{l} I_D = 75 \text{ A}; \ V_{sup} \leq 55 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} = 5 \text{ V}; \ T_{j(\text{init})} = 25 \ ^\circ\text{C}; \ \text{unclamped} \end{array}$ | | - | - | 1.2 | J |

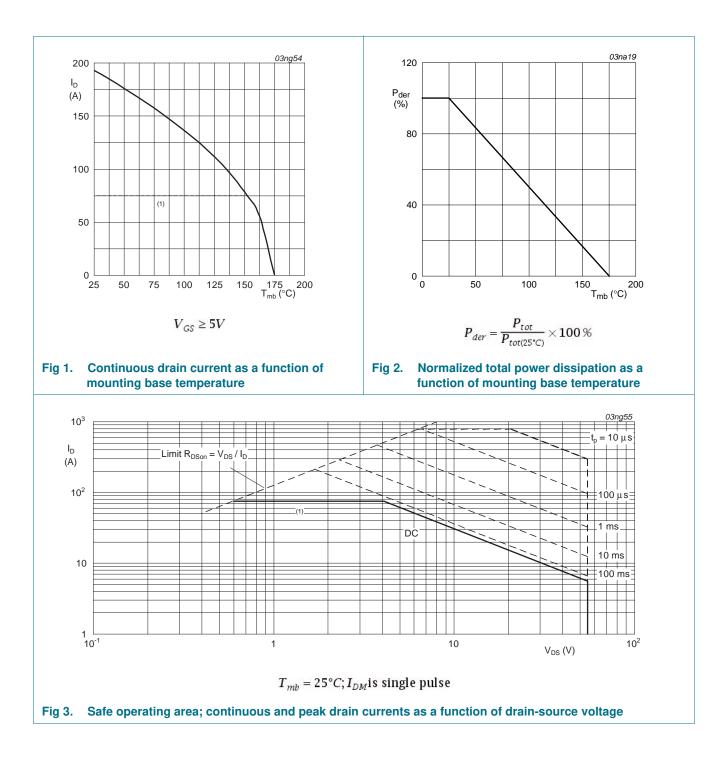
[1] Continuous current is limited by package.

[2] Current is limited by power dissipation chip rating.

[3] Current is limited by power dissipation chip rating.

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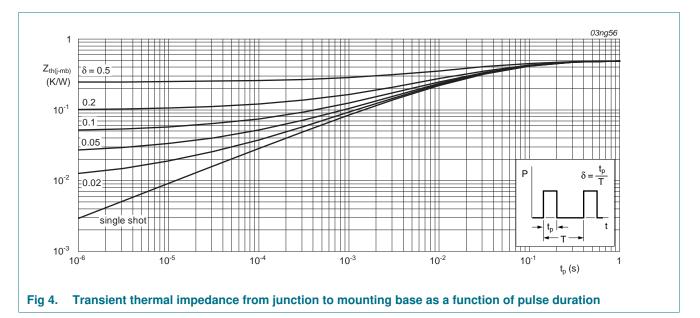
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5. Thermal characteristics

| Table 5. | Thermal characteristics | | | | | |
|----------------------|---|--|-----|-----|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see <mark>Figure 4</mark> | - | - | 0.5 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | minimum footprint ; mounted on a printed circuit-board | - | 50 | - | K/W |



6. Characteristics

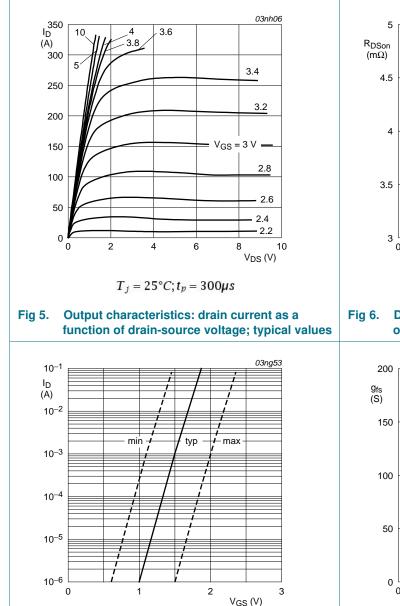
| Table 6. | Characteristics | | | | | |
|---|---|---|-----|------|-------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | aracteristics | | | | | |
| V _{(BR)DSS} | drain-source | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$ | 50 | - | - | V |
| | breakdown voltage | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{V}; \text{T}_\text{j} = 25 ^\circ\text{C}$ | 55 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> | 1.1 | 1.5 | 2 | V |
| | | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 10</u> | - | - | 2.3 | V |
| | | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 10</u> | 0.5 | - | - | V |
| I _{DSS} | drain leakage current | $V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 0.02 | 1 | μA |
| | | $V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$ | - | - | 500 | μA |
| I _{GSS} | gate leakage current | V _{DS} = 0 V; V _{GS} = 15 V; T _j = 25 °C | - | 2 | 100 | nA |
| | | $V_{DS} = 0 \text{ V}; \text{ V}_{GS} = -15 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$ | - | 2 | 100 | nA |
| R _{DSon} drain-source on-state resistance | V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u> | - | 3.5 | 4.2 | mΩ | |
| | | V_{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C | - | - | 4.4 | mΩ |
| | V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 11</u> ; see <u>Figure 12</u> | - | - | 8.4 | mΩ | |
| | | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C | - | 3.1 | 3.7 | mΩ |
| Dynamic | characteristics | | | | | |
| Q _{G(tot)} | total gate charge | $I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 5 \text{ V};$ | - | 95 | - | nC |
| Q _{GS} | gate-source charge | $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{13}$ | - | 17 | - | nC |
| Q _{GD} | gate-drain charge | | - | 37 | - | nC |
| C _{iss} | input capacitance | $V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$ | - | 7665 | 10220 | pF |
| C _{oss} | output capacitance | $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 14}$ | - | 1044 | 1253 | pF |
| C _{rss} | reverse transfer capacitance | | - | 466 | 638 | pF |
| t _{d(on)} | turn-on delay time | $V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$ | - | 63 | - | ns |
| t _r | rise time | $R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$ | - | 232 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 273 | - | ns |
| t _f | fall time | | - | 178 | - | ns |
| L _D internal drain inductance | | from upper edge of drain mounting base to centre of die SOT404 ; $T_j = 25 \text{ °C}$ | - | 2.5 | - | nH |
| | | from drain lead 6 mm from package to centre of die ; $T_j = 25 \text{ °C}$ | - | 4.5 | - | nH |
| L _S | internal source inductance | from source lead to source bond pad ; $T_i = 25 ^\circ\text{C}$ | - | 7.5 | - | nH |

Source-drain diode

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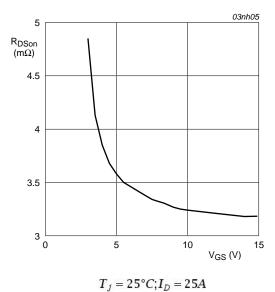
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| Table 6. | Characteristics continued | | | | | |
|-----------------|---------------------------|--|-----|------|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| V_{SD} | source-drain voltage | $I_S = 40 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^\circ\text{C}; \\ \text{see } \underline{\text{Figure 15}}$ | - | 0.85 | 1.2 | V |
| t _{rr} | reverse recovery time | $I_{S} = 20 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu s;$ | - | 78 | - | ns |
| Qr | recovered charge | V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C | - | 171 | - | nC |

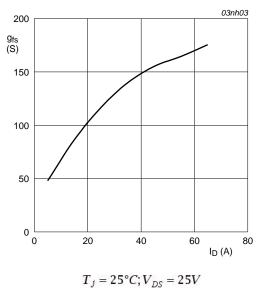


 $T_{j} = 25 \,^{\circ}C; V_{DS} = V_{GS}$





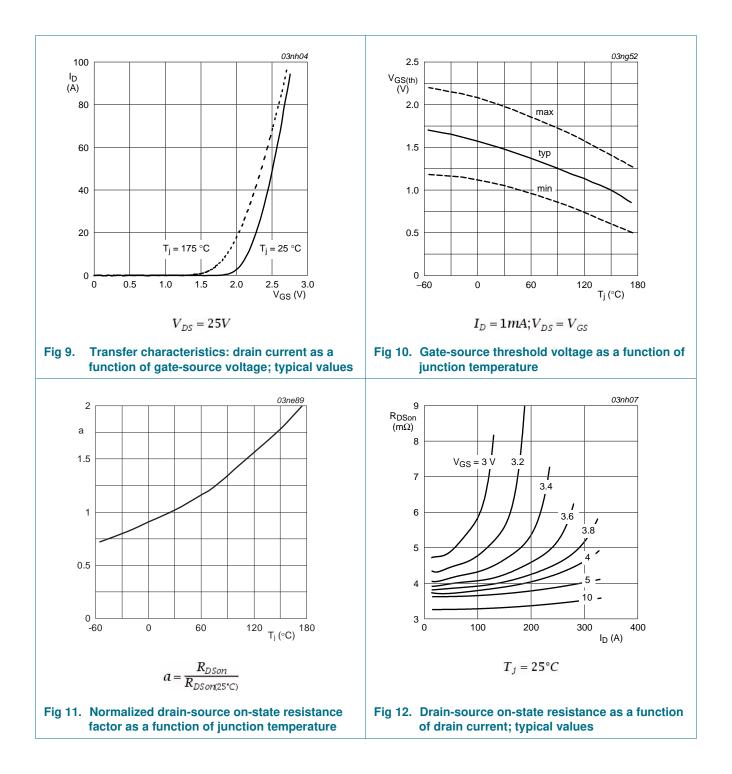






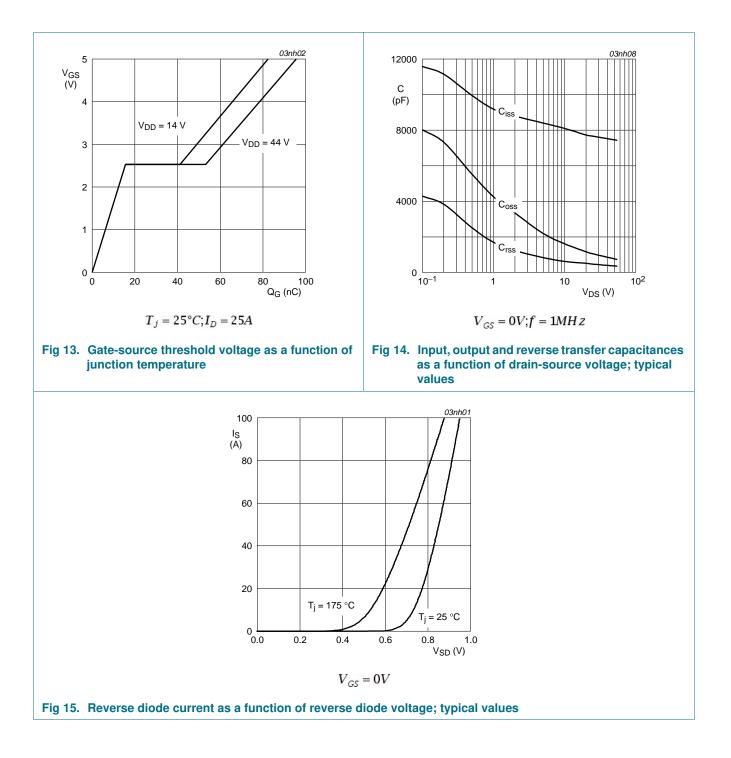
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7. Package outline

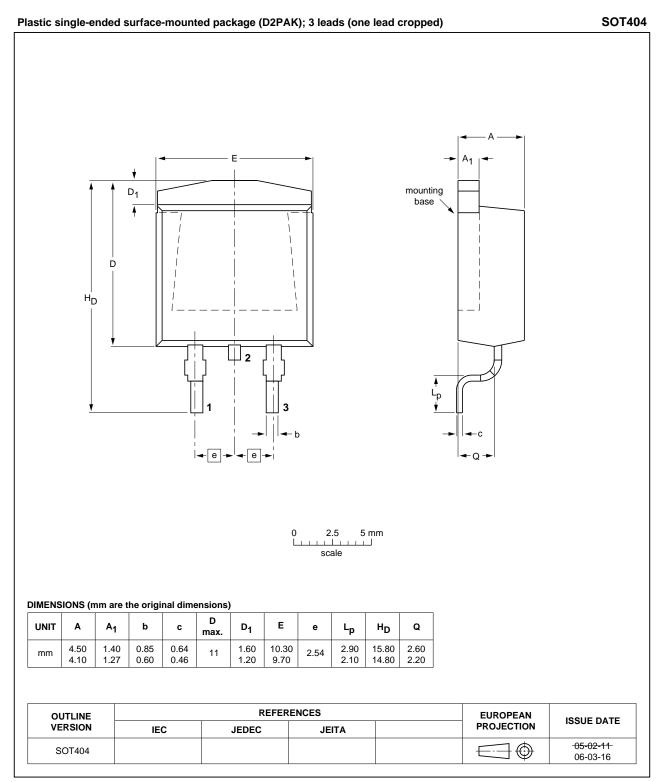


Fig 16. Package outline SOT404 (D2PAK)

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8. Revision history

| Table 7.Revision his | tory | | | |
|--|---------------------------------|---|--------------------------|---------------------------------|
| Document ID | Release date | Data sheet status | Change notice | Supersedes |
| BUK964R2-55B v.3 | 20100604 | Product data sheet | - | BUK95_964R2_55B-02 |
| Modifications: | | of this data sheet has bee niconductors. | n redesigned to comply w | ith the new identity guidelines |
| | Legal texts | have been adapted to the | e new company name wh | ere appropriate. |
| | Type number | er BUK964R2-55B separa | ated from data sheet BUK | (95_964R2_55B-02. |
| BUK95_964R2_55B-02 (9397 750 10277) | 20021008 | Product data | - | - |

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9. Legal information

9.1 Data sheet status

| Document status[1][2] | Product status ^[3] | Definition |
|--------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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